Vishay Semiconductors

Hyperfast Rectifier, 1 A FRED Pt®



SMA (DO-214AC)

LINKS TO ADDITIONAL RESOURCES

30	
3D Models	E

PRIMARY CHARACTERISTICS					
I _{F(AV)}	1 A				
V _R	1200 V				
V _F at I _F	1.10 V				
t _{rr}	75 ns				
T _J max.	175 °C				
Package	SMA (DO-214AC)				
Circuit configuration	Single				

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use as clamp, snubber and freewheeling diode in a flyback aux power supplies, bootstrap and desaturate for HV MOSFET and IGBT driver, high frequency rectifiers in a cuk and sepic circuit for LED lighting.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: SMA (DO-214AC)

Molding compound meets UL 94 V-0 flammability rating **Terminals:** matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V _{RRM}		1200	V		
Average rectified forward current	I _{F(AV)}	T _{Sp} = 144 °C, D = 0.5	1	٨		
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C, 8.3 ms sine pulse	21	A		
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C		

ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	1200	-	-		
		I _F = 1 A	-	1.35	1.80	v	
Forward voltage, per diode	V _F	I _F = 1 A, T _J = 125 °C	-	1.17	1.55		
		I _F = 1 A, T _J = 150 °C	-	1.10	1.44		
Deverse leakage everent, per diede		$V_{R} = V_{R}$ rated	-	-	5		
Reverse leakage current, per diode	I _R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	50	μA	
Junction capacitance	CT	V _R = 1200 V	-	3.5	-	pF	

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COMPLIANT

HALOGEN

FREE





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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS MIN. TYP. I				MAX.	UNITS		
		$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}$	A, I _{rr} = 0.25 A	-	-	75			
Reverse recovery time	t _{rr}	T _J = 25 °C		-	99	-	ns		
		T _J = 125 °C		-	137	-			
Peak recovery current	1	T _J = 25 °C	$I_{\rm F} = 1 {\rm A},$	-	3.5	-	^		
Feak recovery current	I _{RRM}	IRRM	T _J = 125 °C	$dI_F/dt = 200 \text{ A}/\mu \text{s},$ $V_R = 800 \text{ V}$	-	4.5	-	A	
Poverse recovery charge	Q _{rr}	$T_J = 2$	0	T _J = 25 °C		-	150	-	nC
Reverse recovery charge		T _J = 125 °C		-	286	-	nc		

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C	
Thermal resistance, junction to mount	R _{thJM} ⁽¹⁾	Device mounted on PCB with 2 x 3.5 mm soldering lands	-	15	18	°C/W	
Thermal resistance, junction to ambient	R _{thJA}	Device mounted on PCB with recommended pad size	-	110	-	°C/W	
Approximate weight				0.07		g	
Marking device		Case style SMA (DO-214AC)		11	112		

Note

⁽¹⁾ Thermal resistance junction to mount follows JEDEC[®] 51-14 transient dual interface test method (TDIM)



Fig. 1 - Typical Forward Voltage Drop Characteristics



Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage





Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage



Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current



Fig. 5 - Forward Power Loss Characteristics



- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$;
- $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ x \ \mathsf{V}_{\mathsf{FM}} \ at \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ x \ \mathsf{I}_{\mathsf{R}} \ (1 \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ at \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt



Fig. 7 - Typical Stored Charge vs. dl_F/dt



Fig. 8 - I_{rr} (A) vs. dI_F/dt

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t₁ - Rectangular Pulse Duration (s)

Fig. 9 - Transient Thermal Impedance, Junction to Case



Fig. 10 - Reverse Recovery Waveform and Definitions

Notes

⁽¹⁾ di_F/dt - rate of change of current through zero crossing

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- $^{(2)}\ \ I_{RRM}$ peak reverse recovery current
- $^{(3)}$ t_{rr} reverse recovery time measured from t₀, crossing point of negative going I_F, to point t_{10%}, 0.1 I_{RRM}
- $^{(4)}~Q_{rr}$ area under curve defined by t_0 and $t_{10\ \%}$

$$Q_{rr} = \int_{t_0} I(t)dt$$

 $^{(5)}$ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}

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ORDERING INFORMATION TABLE

Device code	VS-	E	7	М	н	01	12	-M3
	1	2	3	4	5	6	7	8
		- Circ	-	niconduo iguration liode		oduct		
	H	- 7 =	•	generatio	on 7			
	5		cess typ hyperfa	oe, ist reco∖	very			
	6	- Cur	rent rati	ng (01 =	= 1 A)			
	7	- Vol	age coo	de (12 =	1200 V)		
	8	- M3	= halog	en-free,	RoHS-	complia	nt, and	termina

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-E7MH0112-M3/I	7500	7500	13"diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95400				
Part marking information	www.vishay.com/doc?95472				
Packaging information	www.vishay.com/doc?95404				
SPICE model	www.vishay.com/doc?97060				



Outline Dimensions

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SMA

DIMENSIONS in inches (millimeters)

DO-214AC (SMA)





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